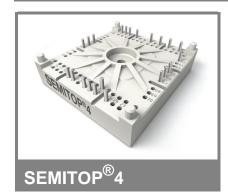
SK 50 DGDL 126 T



3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SK 50 DGDL 126 T

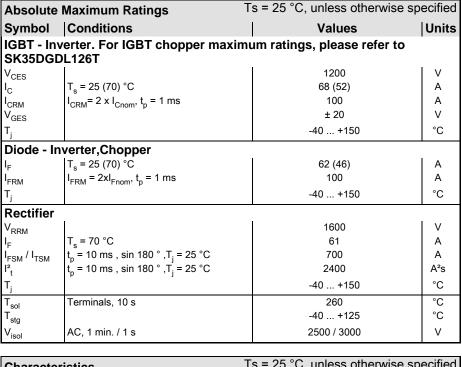
Preliminary Data

Features

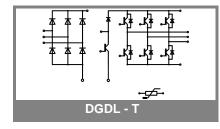
- · One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology free-wheeling diode
- Integrated NTC temperature sensor

Typical Applications

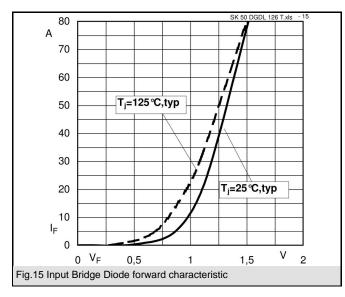
- Inverter up to 28 kVA
- Typ. motor power 15 kW
- 1) $V_{ce,sat}$, $V_f = chip level value$
- For IGBT chopper diagrams please refer to SK35DGDL126T

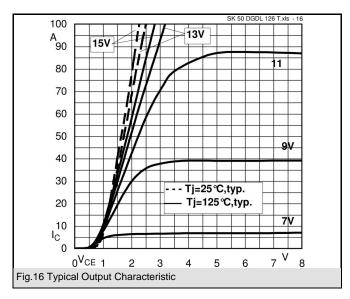


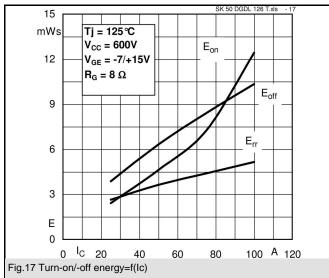
Characteristics		s = 25 °C, unless otherwise specific			
Symbol	Conditions	min.	typ.	max.	Unit
IGBT - In	verter. For IGBT chopper electr	ical charac	teristics,	please ref	er to
SK35DGI					
V_{CEsat}	I _C = 50 A, T _j = 25 (125) °C		1,7 (2)	2,15 (2,45)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 2 \text{ mA}$	5	5,8	6,5	V
$V_{CE(TO)}$	$T_j = 25 ^{\circ}\text{C} (125) ^{\circ}\text{C}$		1 (0,9)	1,2 (1,1)	V
r _T	T _j = 25 °C (125) °C		14 (22)	19 (27)	mΩ
C _{ies}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		3,7		nF
C _{oes}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,18		nF
C _{res}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,16		nF
R _{th(j-s)}	per IGBT		0,6		K/W
t _{d(on)}	under following conditions		115		ns
t _r	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$		28		
$t_{d(off)}$	I _C = 50 A, T _j = 125 °C		509		
<u>t</u>	$R_{Gon} = R_{Goff} = 8 \Omega$		100		
Ė _{on}	inductive load		4,6		
E_{off}			6,3		mJ
Diode - Ir	nverter,Chopper				
V _F = V _{EC}	I _F = 50 A, T _i = 25(125) °C		1,35 (1,35))	V
V _(TO)	T _i = 25 °C (125) °C		0,95 (0,85))	V
r _T	T _j = 25 °C (125) °C		8 (10)		mΩ
R _{th(j-s)}	per diode		1		K/W
I _{RRM}	under following conditions		30		Α
Q _{rr}	I _F = 50 A, V _R = 600 V		10		μC
E _{rr}	V _{GE} = 0 V, T _j = 125 °C		3,6		mJ
	di _{F/dt} = 500 A/µs				
Diode - R	ectifier				
V _F	I _F = 35 A, T _i = 25() °C		1,1		
V _(TO)	T _i = 150 °C		0,8		
r _T	T _i = 150 °C		11		
R _{th(j-s)}	per diode		0,9		
	tur sensor				
R _{ts}	5 %, T _r = 25 (100) °C		5000(493)		Ω
Mechanic	cal data				
w		1	60		g
M _s	Mounting torque	2,5		2,75	Nm
-	7-08-2008 DIL		(C)_	by SEMIK	(ROI

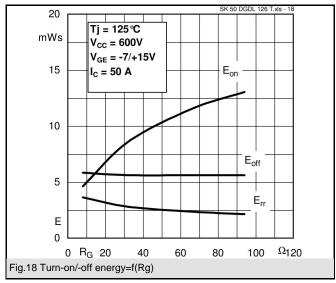


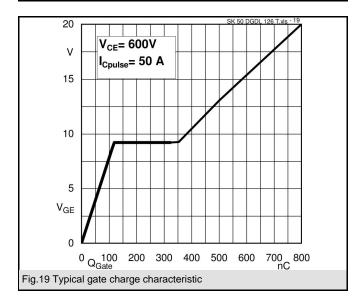
SK 50 DGDL 126 T



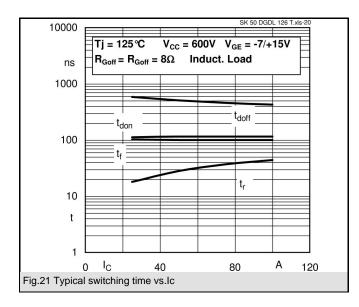


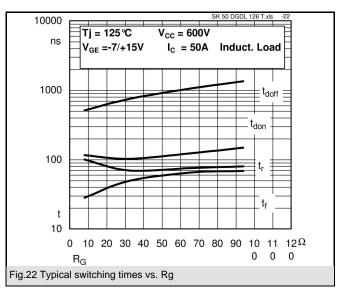


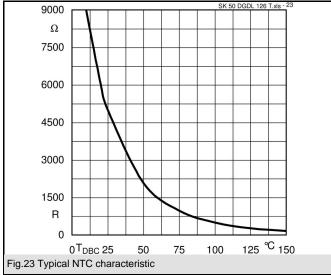


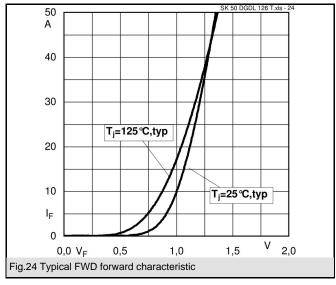


SK 50 DGDL 126 T

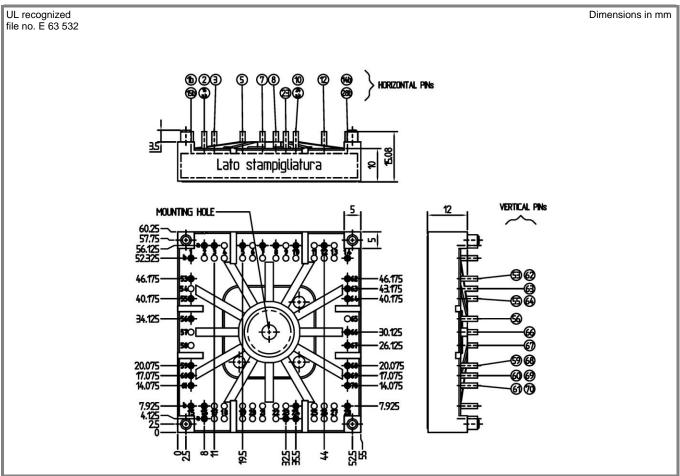




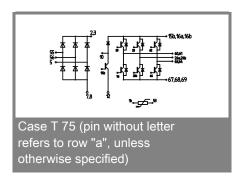




3 27-08-2008 DIL © by SEMIKRON



Case T 75 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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